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Thermal double donors in silicon

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#	Paper	IF	Citations
193	Metastable thermal donor states in germanium: Identification by electron paramagnetic resonance. <i>Physical Review B</i> , 1990 , 42, 9802-9809	3.3	13
192	Comparative study of Si-NL8 and Si-NL10 thermal-donor-related EPR centers. <i>Physical Review B</i> , 1990 , 41, 12628-12636	3.3	31
191	Oxygen-oxygen complexes and thermal donors in silicon. <i>Physical Review B</i> , 1990 , 41, 10595-10603	3.3	21
190	Bistable interstitial-carbon-substitutional-carbon pair in silicon. <i>Physical Review B</i> , 1990 , 42, 5765-5783	3.3	154
189	Metastable defects in silicon: hints for DX and EL2?. <i>Semiconductor Science and Technology</i> , 1991 , 6, B1111-B1204		40
188	Shallow donor in buried oxide Si-On-insulator structures revealed by γ irradiation-induced electron spin resonance activation. 1991 , 78, 321-324		7
187	Infrared absorption of interstitial oxygen in silicon at low temperatures. <i>Applied Physics A: Solids and Surfaces</i> , 1991 , 53, 20-25		21
186	Electron spin resonance of defects in silicon-on-insulator structures formed by oxygen implantation: Influence of γ irradiation. <i>Journal of Applied Physics</i> , 1991 , 69, 175-181	2.5	23
185	New carbon related defects formed in nitrogen rich Czochralski silicon crystals. <i>Applied Physics Letters</i> , 1991 , 59, 1890-1892	3.4	2
184	Silicon-interstitial-oxygen-interstitial complex as a model of the 450 degrees C oxygen thermal donor in silicon. <i>Physical Review Letters</i> , 1991 , 66, 747-749	7.4	25
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174	Hydrogen Passivation and Reactivation of Bistable Thermal Donors in Silicon. 1992 , 262, 395		1
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